



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

5 A

Features

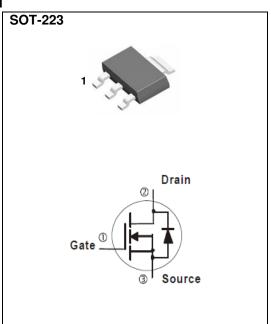
- R_{DS(ON)}, V_{GS}@10V, I_D@5A<75mΩ
- $R_{DS(ON)}$, V_{GS} @4.5V, I_{D} @3A<90m Ω
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: SOT-223 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.043 ounces, 0.123grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	- v	
Gate-Source Voltage		V_{GS}	<u>+</u> 20		
Continuous Drain Current (Note 4)	T _A =25°C		5	A	
	T _A =70°C	l _D	4		
Pulsed Drain Current (Note 1)		I _{DM}	20		
Power Dissipation	T _A =25°C	P_D	3.72	W	
	T _A =70°C		2.61		
Operating Junction and Storage Temperature Range		T_{J},T_{STG}	-55~175	°C	
Typical Thermal Resistance					
- Junction to Ambient (Note 4,5)		$R_{\theta JA}$	40.3	°C/W	

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	60	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1	1.8	2.5			
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =10V, I_D =5A	-	53	75			
		V_{GS} =4.5V, I_D =3A	-	61	90	mΩ		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =60V, V_{GS} =0V	-	-	1	uA		
Gate-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA		
Dynamic (Note 6)								
Total Gate Charge	Qg	V _{DS} =48V, I _D =3A, V _{GS} =10V ^(Note 2,3)	-	9.3	-	nC		
Gate-Source Charge	Q_{gs}		-	2.2	-			
Gate-Drain Charge	Q_{gd}		-	1.9	-			
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V,	-	509	-	pF		
Output Capacitance	Coss		-	47	-			
Reverse Transfer Capacitance	Crss	f=1MHZ	-	23	-			
Turn-On Delay Time	td _(on)	$V_{DD}{=}30V, I_{D}{=}3A, \ V_{GS}{=}10V, \ R_{G}{=}3.3\Omega^{(Note 2,3)}$	-	3.2	-			
Turn-On Rise Time	t _r		-	9.7	-	ns		
Turn-Off Delay Time	td _(off)		-	18.5	-			
Turn-Off Fall Time	t _f	H _G =3.312	-	6.4	-			
Drain-Source Diode								
Maximum Continuous Drain-Source								
Diode Forward Current	I _S		-	-	5	Α		
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.75	1	V		

NOTES:

- 1. Pulse width <300us, Duty cycle <2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

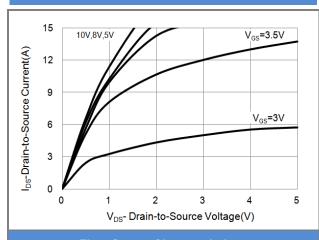


Fig.1 Output Characteristics

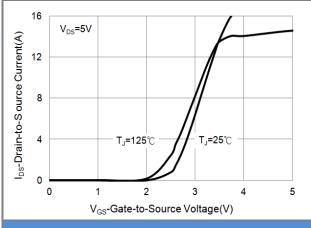


Fig.2 Transfer Characteristics

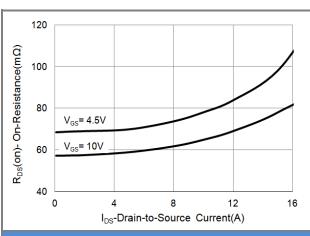


Fig.3 On-Resistance vs. Drain Current

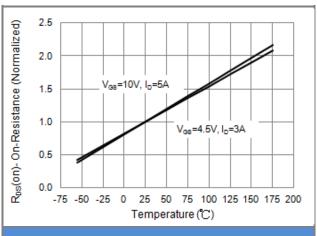


Fig.4 On-Resistance vs. Junction temperature

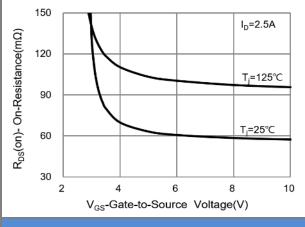


Fig.5 On-Resistance Variation with V_{GS}

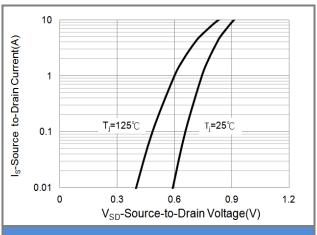


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

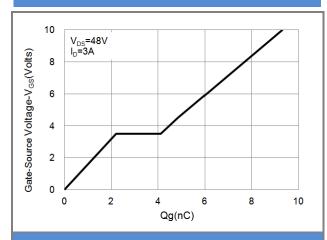


Fig.7 Gate-Charge Characteristics

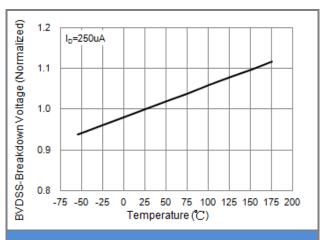


Fig.8 Breakdown Voltage Variation vs. Temperature

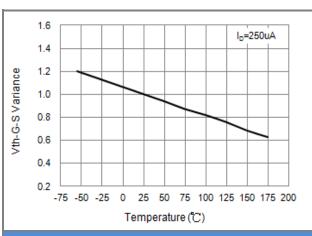


Fig.9 Threshold Voltage Variation with Temperature

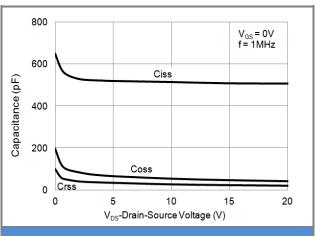


Fig.10 Capacitance vs. Drain-Source Voltage

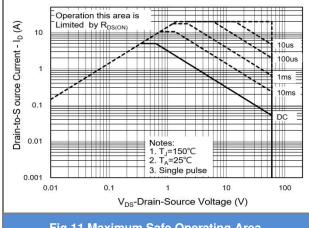


Fig.11 Maximum Safe Operating Area

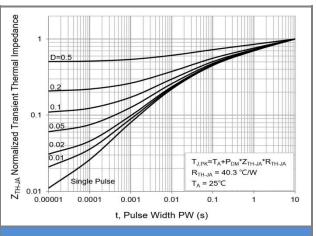


Fig.12 Normalized Transient Thermal Impedance

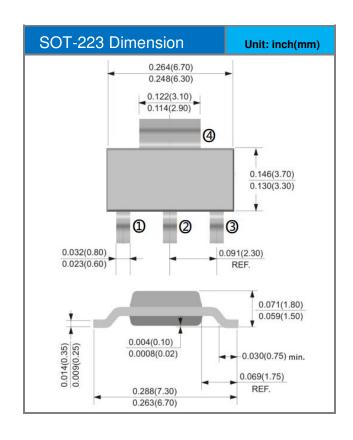


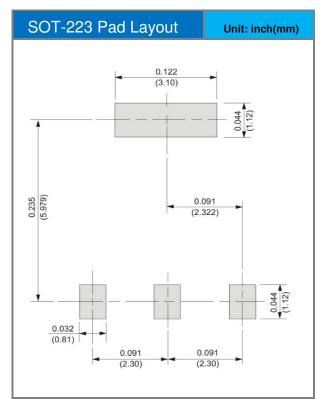


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJW5N06A-AU_R2_000A1	SOT-223	2,500pcs / 13" reel	W5N06A	Halogen free

Packaging Information & Mounting Pad Layout









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